

AMENDMENTS TO THE SPECIFICATION:

Page 22, replace the paragraph, beginning on line 21, bridging pages 22 and 23, with the following amended paragraph:

--Specifically, the gate electrodes ~~6a~~ 16a are formed on the plate 14 and then, the dielectric protection layer 15 is formed on the plate 14 to cover the gate electrodes 16a. Thereafter, the semiconductor layers 16c are formed on the layer 15 to be overlapped with the corresponding gate electrodes 16a. Furthermore, the drain and source electrodes 16b and 16c are formed on the layer 15 to contact with the corresponding semiconductor layers 16c, resulting in the TFTs 16. Finally, the first dielectric layer 17 is formed to cover the TFTs 16 thus formed and then, the contact holes 17a are formed to penetrate the same. The source electrodes 16d are exposed from the layer 17 by way of the holes 17a. The state at this stage is shown in Fig. 4A.--